

preliminary data

$$I_{FAVM} = 2 \times 128 \text{ A}$$

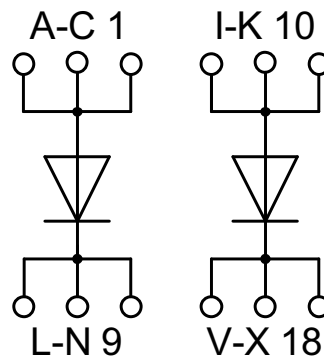
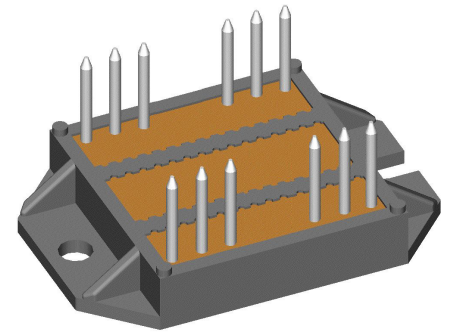
$$V_{RRM} = 1200 \text{ V}$$

$$t_{rr} = 40 \text{ ns}$$

Fast Recovery Epitaxial Diode (FRED)

Part number

DSEI2x161-12P



Features / Advantages:

- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Leads suitable for PC board soldering
- Very short recovery time
- Soft recovery behaviour
- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Low noise switching
- Small and light weight

Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Package: ECO-PAC2

- Isolation voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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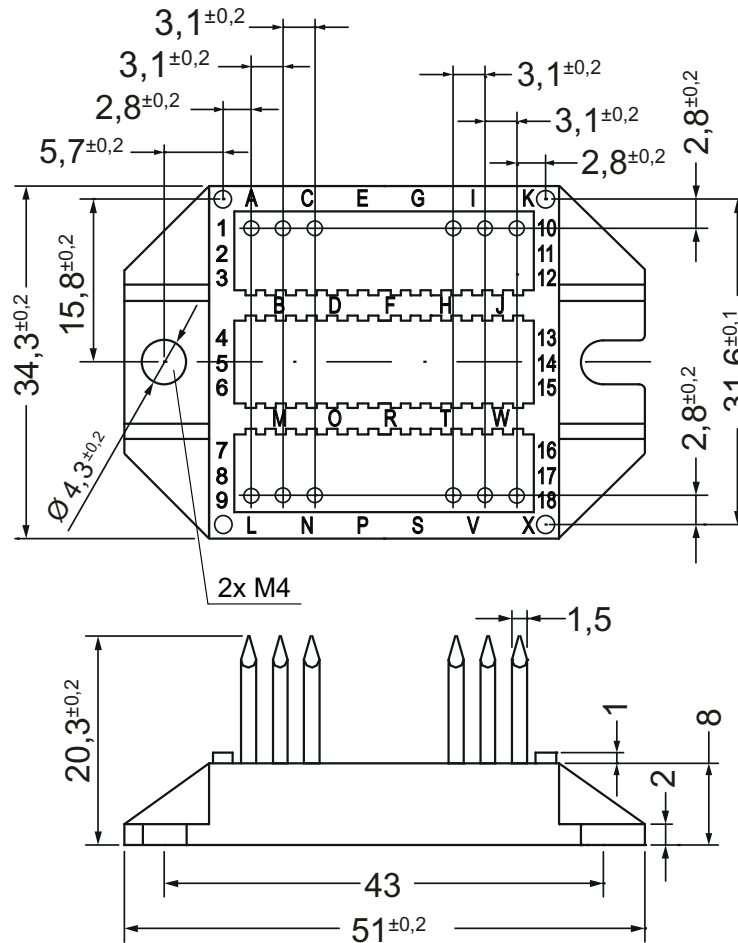
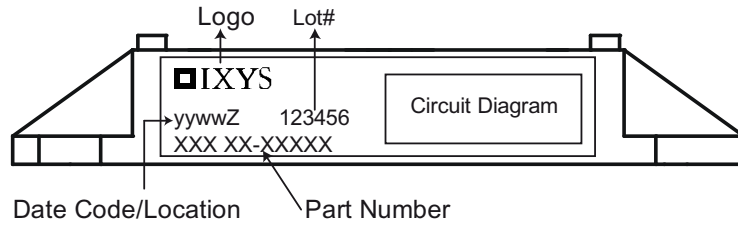
Diode			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{FRMS}	RMS forward current				270	A
I_{FAVM} ①	max. average forward current	rectangular, d = 0.5			128	A
I_{FSM}	max. surge forward current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		1200	A
		t = 8.3 ms (60 Hz), sine			1300	A
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$		1080	A
		t = 8.3 ms (60 Hz), sine			1170	A
I^2t	I^2t value for fusing	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		7200	A ² s
		t = 8.3 ms (60 Hz), sine			7100	A ² s
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$		5800	A ² s
		t = 8.3 ms (60 Hz), sine			5700	A ² s
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		12	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		3	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 125^{\circ}\text{C}$		60	mA
V_F	forward voltage	$I_F = 200$ A	$T_{VJ} = 25^{\circ}\text{C}$		1.9	V
V_{TO}	threshold voltage	for power-loss calculations only	$T_{VJ} = T_{VJM}$		1.16	V
r_T	slope resistance				3	mΩ
R_{thJC}	thermal resistance junction to case			0.20	0.29	K/W
R_{thCH}	thermal resistance junction to heatsink					K/W
I_{RM}	max. reverse recovery current	$I_F = 100$ A; $-di_F/dt = 200$ A/μs $V_R = 100$ V; $L \leq 0.05$ μH	$T_{VJ} = 100^{\circ}\text{C}$		48	A
t_{rr}	reverse recovery time	$I_F = 1$ A; $-di/dt = 400$ A/μs; $V_R = 30$ V	$T_{VJ} = 25^{\circ}\text{C}$		40	ns

 ① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle d = 0.5



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Package ECO-PAC2			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				24		g
M_D	mounting torque		1.4		2.0	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Appb}$			terminal to backside	10.0		
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V V
			50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA			



IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified.

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